**Thyristor Module** 

## MCMA265P1600KA

### preliminary

| $V_{\text{RRM}}$ | <i>=</i> 2x 1600 V |        |  |
|------------------|--------------------|--------|--|
| I <sub>tav</sub> | =                  | 260 A  |  |
| V <sub>T</sub>   | =                  | 1.15 V |  |

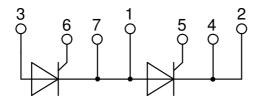
Phase leg

Part number

MCMA265P1600KA



Backside: isolated **E**72873



#### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

### **Applications:**

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

#### Package: Y1

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper
- internally DCB isolated
- Advanced power cycling

#### Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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# LIXYS

# MCMA265P1600KA

## preliminary

| Thyristo                 |                                    |  |  | 1    | Ratings | 1     | !                 |
|--------------------------|------------------------------------|--|--|------|---------|-------|-------------------|
| Symbol                   | Definition                         | Conditions   |  | min. | typ.    | max.  | Uni               |
| V <sub>RSM/DSM</sub>     | max. non-repetitive reverse/forwa  |  | $T_{VJ} = 25^{\circ}C$                             |      |         | 1700  | ١                 |
| V <sub>RRM/DRM</sub>     | max. repetitive reverse/forward bl |  | $T_{VJ} = 25^{\circ}C$                             |      |         | 1600  | ١                 |
| R/D                      | reverse current, drain current     | $V_{R/D} = 1600 V$   | $T_{vJ} = 25^{\circ}C$                             |      |         | 300   | μA                |
|                          |                                    | V <sub>R/D</sub> = 1600 V  | $T_{VJ} = 140^{\circ}C$                            |      |         | 30    | mA                |
| V <sub>T</sub>           | forward voltage drop               | $I_{T} = 300 \text{ A}$  | $T_{VJ} = 25^{\circ}C$                             |      |         | 1.19  | ١                 |
|                          |                                    | $I_{T} = 600 \text{ A}$  |  |      |         | 1.46  | ١                 |
|                          |                                    | $I_{T} = 300 \text{ A}$  | $T_{VJ} = 125 \degree C$                           |      |         | 1.15  | ١                 |
|                          |                                    | $I_{T} = 600 \text{ A}$  |  |      |         | 1.44  | ١                 |
| ITAV                     | average forward current            | $T_c = 85^{\circ}C$  | T <sub>vJ</sub> = 140°C                            |      |         | 260   | ŀ                 |
| T(RMS)                   | RMS forward current                | 180° sine  |  |      |         | 408   | ļ                 |
| V <sub>T0</sub>          | threshold voltage                  |  | T <sub>v.i</sub> = 140°C                           |      |         | 0.80  | ١                 |
| r <sub>T</sub>           | slope resistance } for power lo    | oss calculation only   |  |      |         | 0.75  | mΩ                |
| <b>R</b> <sub>thJC</sub> | thermal resistance junction to cas | e  |  |      |         | 0.16  | K/W               |
| R <sub>thCH</sub>        | thermal resistance case to heatsi  |  |  |      | 0.04    |       | K/W               |
| P <sub>tot</sub>         | total power dissipation            |  | $T_c = 25^{\circ}C$                                |      | 0.0.    | 720   | W                 |
| I <sub>TSM</sub>         | max. forward surge current         | t = 10 ms; (50 Hz), sine   | $T_{v_{i}} = 45^{\circ}C$                          |      |         | 8.50  | k/                |
| ISM                      |                                    | t = 8,3 ms; (60 Hz), sine  | $V_{\rm N} = 0 V$                                  |      |         | 9.18  | k/                |
|                          |                                    | t = 0,0  ms; (50  Hz),  sine<br>t = 10  ms; (50  Hz),  sine                | $\frac{V_{R}}{T_{V,l}} = 140^{\circ}C$             |      |         | 7.23  | k/                |
|                          |                                    | t = 8,3  ms; (60  Hz),  sine   | $V_{\rm NJ} = 140$ C<br>$V_{\rm R} = 0$ V          |      |         | 7.81  | k/                |
| 124                      | value for fusing                   |  | $V_{R} = 0 V$ $T_{VJ} = 45^{\circ}C$               |      |         |       | 1                 |
| l²t                      | value for fusing                   | t = 10 ms; (50 Hz), sine   |  |      |         | 361.3 | 1                 |
|                          |                                    | t = 8,3 ms; (60 Hz), sine  | $V_{\rm R} = 0 V$                                  |      |         | 350.6 |                   |
|                          |                                    | t = 10 ms; (50 Hz), sine   | $T_{VJ} = 140 ^{\circ}C$                           |      |         | 261.0 | kA <sup>2</sup> s |
|                          | ·                                  | t = 8,3 ms; (60 Hz), sine  | $V_{\rm R} = 0 V$                                  |      |         | 253.4 |                   |
| C                        | junction capacitance               | $V_{R} = 400 V f = 1 MHz$  | $T_{VJ} = 25^{\circ}C$                             |      | 366     |       | pF                |
| P <sub>GM</sub>          | max. gate power dissipation        | t <sub>P</sub> = 30 μs   | $T_{\rm C} = 140^{\circ}{\rm C}$                   |      |         | 120   | W                 |
|                          |                                    | t <sub>P</sub> = 500 μs  |  |      |         | 60    | N                 |
| P <sub>GAV</sub>         | average gate power dissipation     |  |  |      |         | 20    | N                 |
| (di/dt) <sub>cr</sub>    | critical rate of rise of current   | $T_{vJ} = 140 ^{\circ}C; f = 50  Hz$ re                                    | epetitive, $I_T = 750 \text{ A}$                   |      |         | 100   | A/μs              |
|                          |                                    | $t_{P} = 200 \mu s; di_{G}/dt = 1 A/\mu s;$                                |  |      |         |       | :<br>:<br>:<br>:  |
|                          |                                    | $I_{G} = 1 \text{ A}; \text{ V} = \frac{2}{3} \text{ V}_{DRM} $ n          | on-repet., $I_{T} = 268 \text{ A}$                 |      |         | 500   | A/μs              |
| (dv/dt) <sub>cr</sub>    | critical rate of rise of voltage   | $V = \frac{2}{3} V_{DRM}$  | $T_{vJ} = 140^{\circ}C$                            |      |         | 1000  | V/µs              |
|                          |                                    | $R_{GK} = \infty$ ; method 1 (linear volta                                 | age rise)  |      |         |       | 1<br>1<br>1<br>1  |
| V <sub>gt</sub>          | gate trigger voltage               | $V_{D} = 6 V$  | $T_{vJ} = 25^{\circ}C$                             |      |         | 2     | V                 |
|                          |                                    |  | $T_{vJ} = -40 ^{\circ}C$                           |      |         | 3     | V                 |
| I <sub>GT</sub>          | gate trigger current               | $V_{D} = 6 V$  | $T_{vJ} = 25^{\circ}C$                             |      |         | 150   | mA                |
|                          |                                    |  | $T_{vJ} = -40 ^{\circ}\text{C}$                    |      |         | 220   | mA                |
| V <sub>gd</sub>          | gate non-trigger voltage           | $V_{D} = \frac{2}{3} V_{DBM}$  | T <sub>vJ</sub> = 140°C                            |      |         | 0.25  | V                 |
|                          | gate non-trigger current           |  | 10   |      |         | 10    | mA                |
| IL                       | latching current                   | t <sub>p</sub> = 30 μs   | $T_{vJ} = 25 °C$                                   |      |         | 200   | mA                |
| 1                        |                                    | $I_{g} = 0.45 \text{ A}; \text{ di}_{g}/\text{dt} = 0.45 \text{ A}/\mu$    |  |      |         | 200   |                   |
| I <sub>H</sub>           | holding current                    | $V_{\rm D} = 6 V R_{\rm GK} = \infty$                                      | $T_{vJ} = 25 ^{\circ}C$                            |      |         | 150   | m/                |
|                          |                                    |  | $T_{VJ} = 25 \text{ C}$<br>$T_{VJ} = 25 \text{ C}$ |      |         |       | 1                 |
| t <sub>gd</sub>          | gate controlled delay time         | $V_{\rm D} = \frac{1}{2} V_{\rm DRM}$                                      |  |      |         | 2     | μ                 |
| -                        | turn all the -                     | $I_{\rm G} = 1 {\rm A};  {\rm di}_{\rm G}/{\rm dt} = 1 {\rm A}/\mu{\rm s}$ |  |      |         |       | :<br>:<br>:<br>:  |
| t <sub>q</sub>           | turn-off time                      | $V_{R} = 100 \text{ V}; I_{T} = 300 \text{ A}; \text{ V} = \frac{2}{3}$    |  |      | 200     |       | με                |
|                          |                                    | $di/dt = 10 \text{ A}/\mu \text{s} dv/dt = 50 \text{ V}$                   | //μs  t <sub>p</sub> = 200 μs                      |      |         |       |                   |

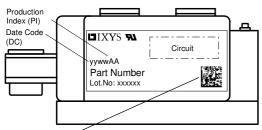
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# XYS

# MCMA265P1600KA

preliminary

| Package Y1                  |  |                   |                             |      | Ratings |      |      |  |
|-----------------------------|--|-------------------|-----------------------------|------|---------|------|------|--|
| Symbol                      | Definition                                   | Conditions        |                             | min. | typ.    | max. | Unit |  |
| I <sub>RMS</sub>            | RMS current                                  | per terminal      |                             |      |         | 600  | Α    |  |
| T <sub>vj</sub>             | virtual junction temperature                 |                   |                             | -40  |         | 140  | °C   |  |
| T <sub>op</sub>             | operation temperature                        |                   |                             | -40  |         | 125  | °C   |  |
| T <sub>stg</sub>            | storage temperature                          |                   |                             | -40  |         | 125  | °C   |  |
| Weight                      |  |                   |                             |      | 680     |      | g    |  |
| M <sub>D</sub>              | mounting torque                              |                   |                             | 4.5  |         | 7    | Nm   |  |
| M <sub>T</sub>              | terminal torque                              |                   |                             | 11   |         | 13   | Nm   |  |
| d <sub>Spp/App</sub>        | creepage distance on surface   striking dist | tanaa thraugh air | terminal to terminal        | 16.0 |         |      | mm   |  |
| <b>d</b> <sub>Spb/Apb</sub> |  | stance infough an | terminal to backside        | 16.0 |         |      | mm   |  |
| V                           | isolation voltage                            | t = 1 second      |                             | 4800 |         |      | V    |  |
|                             |  | t = 1 minute      | 50/60 Hz, RMS; liso∟ ≤ 1 mA | 4000 |         |      | V    |  |



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

#### Part description

M = Module

C = Thyristor (SCR)M = Thyristor

A = (up to 1800V) 265 = Current Rating [A] P = Phase leg

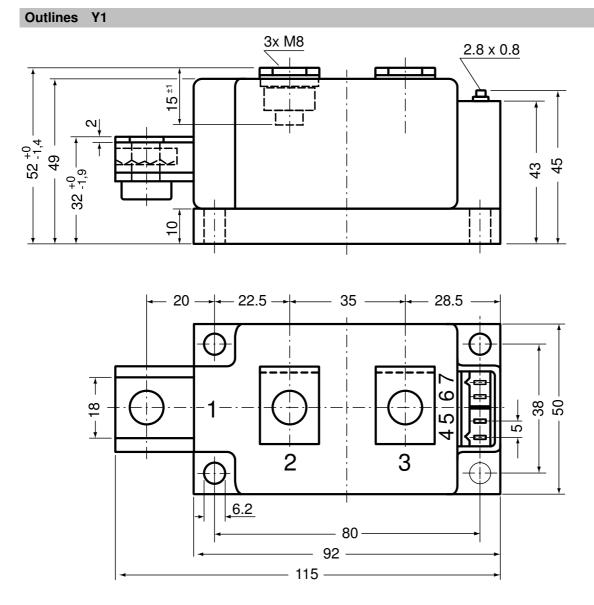
1600 = Reverse Voltage [V] KA = Y1-CU

| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | MCMA265P1600KA  | MCMA265P1600KA     | Box           | 3        | 509792   |

| Equiva                       | alent Circuits for | Simulation | * on die level | T <sub>vj</sub> = 140 °C |
|------------------------------|--------------------|------------|----------------|--------------------------|
|                              | $-R_{o}-$          | Thyristor  |                |                          |
| V <sub>0 max</sub>           | threshold voltage  | 0.8        |                | V                        |
| $\mathbf{R}_{0 \text{ max}}$ | slope resistance * | 0.51       |                | mΩ                       |

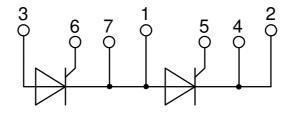
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Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red Type ZY 180L (L = Left for pin pair 4/5) Type ZY 180R (R = Right for pin pair 6/7) UL 758, style 3751



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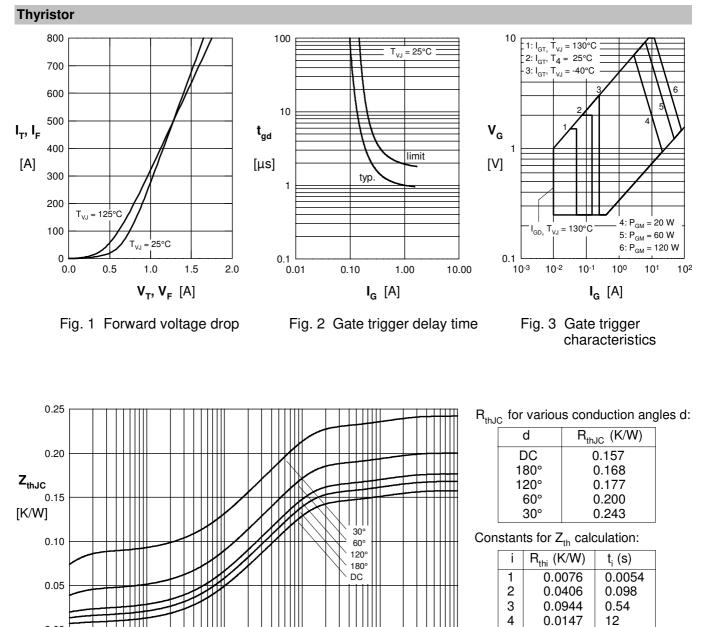


Fig. 4 Transient thermal impedance junction to case (per thyristor/diode)

t [s]

100

10<sup>1</sup>

10<sup>2</sup>

10-1

10-2

0.00

10-3